

ABSTRACT

A method for manufacturing a semiconductor device of the present invention includes a first wire bonding step of electrically connecting a first semiconductor element onto a substrate via a first wire, a pressure bonding step of pressure-bonding a second semiconductor element to the substrate via an adhesive having a thermosetting property, and a heating and pressurizing step of heating the adhesive after the pressure bonding step under a pressurized atmosphere to subject the adhesive to a curing treatment. Through the heating and pressurizing step, at least one of at least a part of the first wire and the first semiconductor element is embedded in the adhesive after the curing treatment. A melt viscosity at 120°C of the adhesive before the curing treatment is 1000 to 3000 Pa·s.

Fig. 6